STARPOWER

SEMICONDUCTOR **IGBT**

GD15PHX120L2S

1200V/15A in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

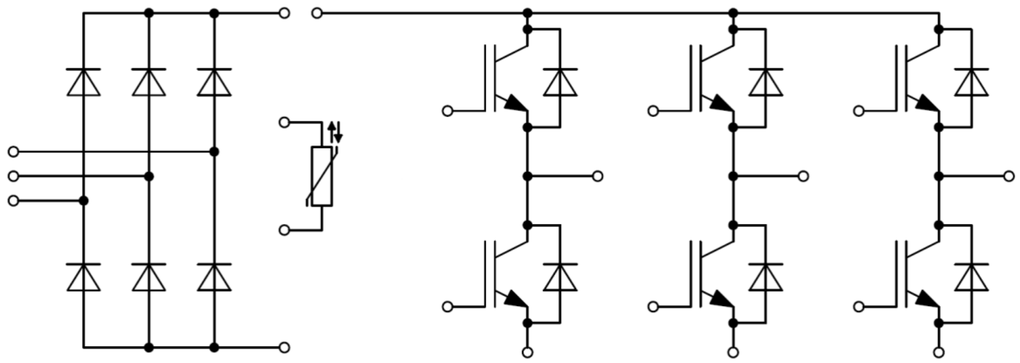
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10μs short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT-inverter

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=25°C @ T_C=100°C	30 15	A
I_{CM}	Pulsed Collector Current t_p=1ms	30	A
P_D	Maximum Power Dissipation @ T_j=175°C	168	W

Diode-inverter

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	15	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	30	A

Diode-rectifier

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
I_O	Average Output Current 50Hz/60Hz,sine wave	15	A
I_{FSM}	Surge Forward Current t_p=10ms @ T_j=25°C @ T_j=150°C	300 245	A
I^2t	I^2t-value,t_p=10ms @ T_j=25°C @ T_j=150°C	450 300	A^2s

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature(inverter) Maximum Junction Temperature (rectifier)	175 150	°C
T_{jop}	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	2500	V

IGBT-inverter Characteristics $T_C=25^oC$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=15A, V_{GE}=15V, T_j=25^oC$		1.70	2.15	V
		$I_C=15A, V_{GE}=15V, T_j=125^oC$		1.95		
		$I_C=15A, V_{GE}=15V, T_j=150^oC$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.38mA, V_{CE}=V_{GE}, T_j=25^oC$	5.2	6.0	6.8	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0V, T_j=25^oC$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0V, T_j=25^oC$			400	nA
R_{Gint}	Internal Gate Resistance			0		Ω
C_{ies}	Input Capacitance	$V_{CE}=25V, f=1MHz, V_{GE}=0V$		1.55		nF
C_{res}	Reverse Transfer Capacitance			0.04		nF
Q_G	Gate Charge	$V_{GE}=-15…+15V$		0.12		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=15A, R_G=39\Omega, V_{GE}=\pm15V, T_j=25^oC$		59		ns
t_r	Rise Time			63		ns
$t_{d(off)}$	Turn-Off Delay Time			201		ns
t_f	Fall Time			149		ns
E_{on}	Turn-On Switching Loss			1.39		mJ
E_{off}	Turn-Off Switching Loss			0.85		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=15A, R_G=39\Omega, V_{GE}=\pm15V, T_j=125^oC$		59		ns
t_r	Rise Time			70		ns
$t_{d(off)}$	Turn-Off Delay Time			283		ns
t_f	Fall Time			196		ns
E_{on}	Turn-On Switching Loss			1.87		mJ
E_{off}	Turn-Off Switching Loss			1.24		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=15A, R_G=39\Omega, V_{GE}=\pm15V, T_j=150^oC$		59		ns
t_r	Rise Time			70		ns
$t_{d(off)}$	Turn-Off Delay Time			288		ns
t_f	Fall Time			221		ns
E_{on}	Turn-On Switching Loss			2.09		mJ
E_{off}	Turn-Off Switching Loss			1.39		mJ
I_{SC}	SC Data	$t_P\leq10\mu s, V_{GE}=15V, T_j=150^oC, V_{CC}=900V, V_{CEM}\leq1200V$		60		A

Diode-inverter Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	I_F=15A,V_{GE}=0V,T_j=25°C		1.85	2.30	V
		I_F=15A,V_{GE}=0V,T_j=125°C		1.90		
		I_F=15A,V_{GE}=0V,T_j=150°C		1.95		
Q_r	Recovered Charge	V_R=600V,I_F=15A, -di/dt=540A/µs,V_{GE}=-15V T_j=25°C		1.4		µC
I_{RM}	Peak Reverse Recovery Current			15		A
E_{rec}	Reverse Recovery Energy			0.36		mJ
Q_r	Recovered Charge	V_R=600V,I_F=15A, -di/dt=540A/µs,V_{GE}=-15V T_j=125°C		2.4		µC
I_{RM}	Peak Reverse Recovery Current			14		A
E_{rec}	Reverse Recovery Energy			0.67		mJ
Q_r	Recovered Charge	V_R=600V,I_F=15A, -di/dt=540A/µs,V_{GE}=-15V T_j=150°C		2.8		µC
I_{RM}	Peak Reverse Recovery Current			14		A
E_{rec}	Reverse Recovery Energy			0.78		mJ

Diode-rectifier Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	I_F=15A,T_j=150°C		0.85		V
I_R	Reverse Current	T_j=150°C,V_R=1600V			2.0	mA

NTC Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		kΩ
ΔR/R	Deviation of R_{100}	T_C=100 °C,R_{100}=493.3Ω	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}exp[B_{25/80}(1/T_2-1/(298.15K))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}exp[B_{25/100}(1/T_2-1/(298.15K))]$		3433		K

Module Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		30		nH
$R_{CC'+EE'}$ $R_{AA'+CC'}$	Module Lead Resistance,Terminal to Chip		8.00 6.00		mΩ
R_{thJC}	Junction-to-Case (per IGBT-inverter) Junction-to-Case (per Diode-inverter) Junction-to-Case (per Diode-rectifier)		0.808 1.309 0.845	0.889 1.440 0.930	K/W
R_{thCH}	Case-to-Heatsink (per IGBT-inverter) Case-to-Heatsink (per Diode-inverter) Case-to-Heatsink (per Diode-rectifier) Case-to-Heatsink (per Module)		0.895 1.451 0.937 0.058		K/W
F	Mounting Force Per Clamp	20		50	N
G	Weight of Module		24		g

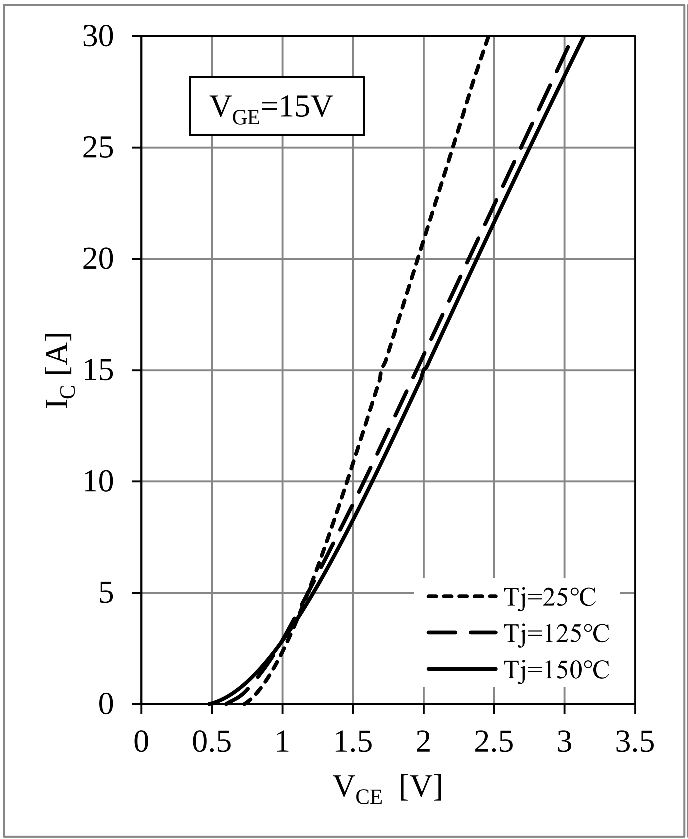


Fig 1. IGBT-inverter Output Characteristics

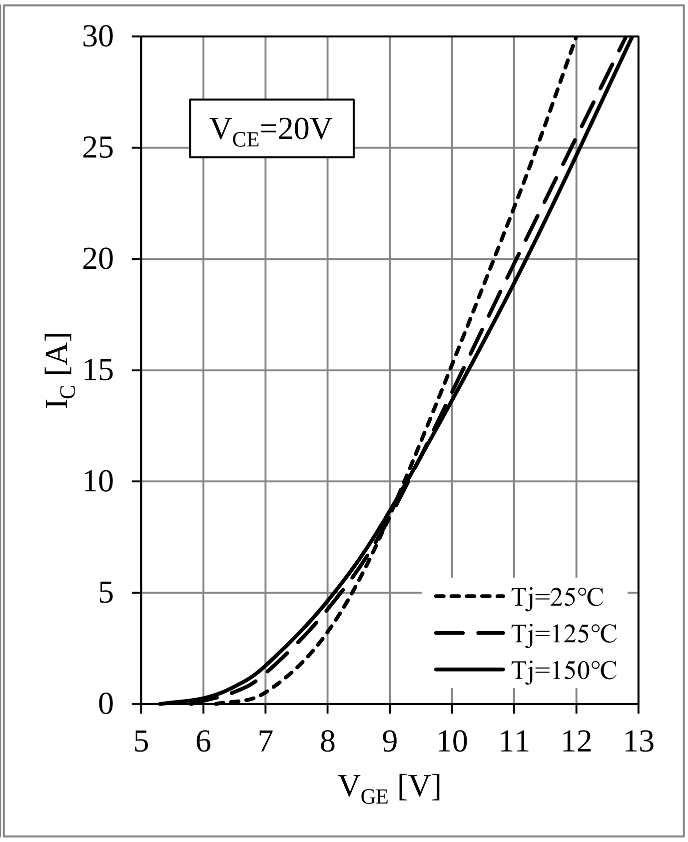


Fig 2. IGBT-inverter Transfer Characteristics

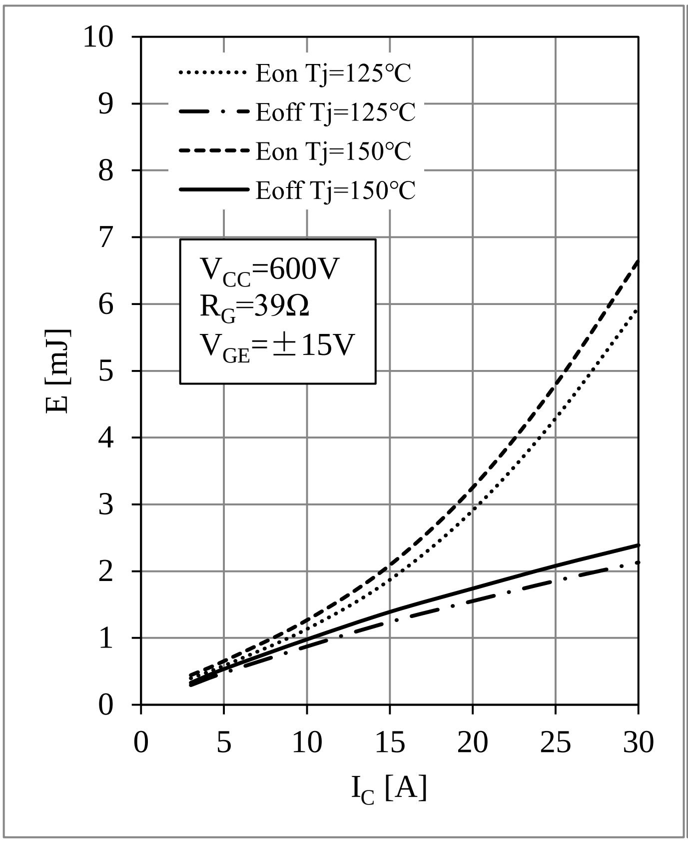


Fig 3. IGBT-inverter Switching Loss vs. I_C

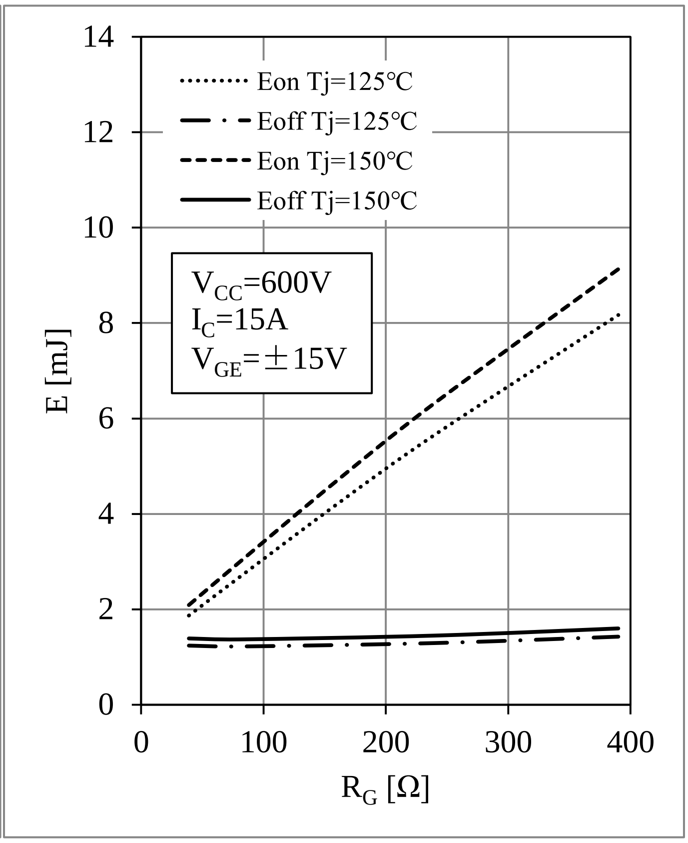


Fig 4. IGBT-inverter Switching Loss vs. R_G

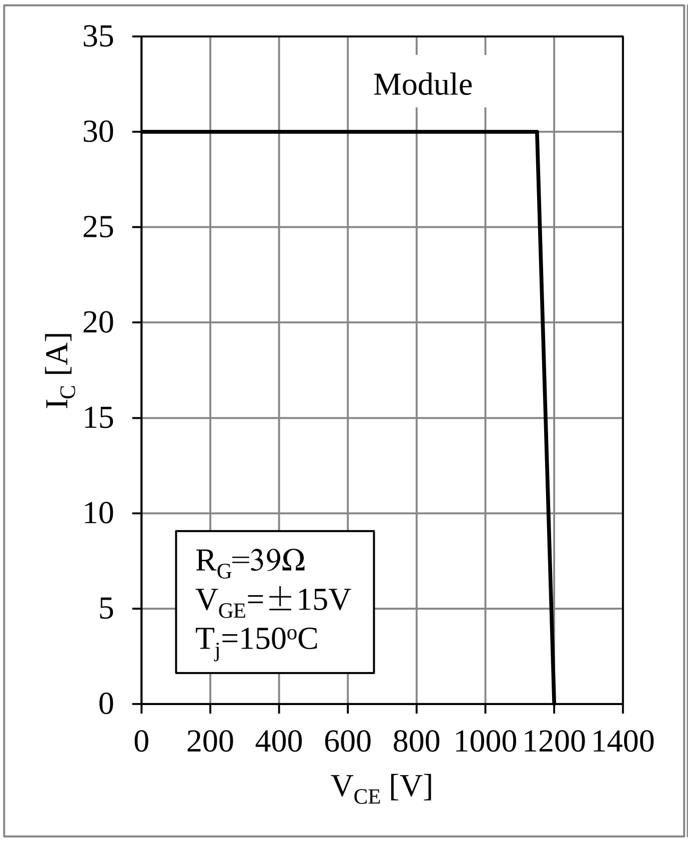


Fig 5. IGBT-inverter RBSOA

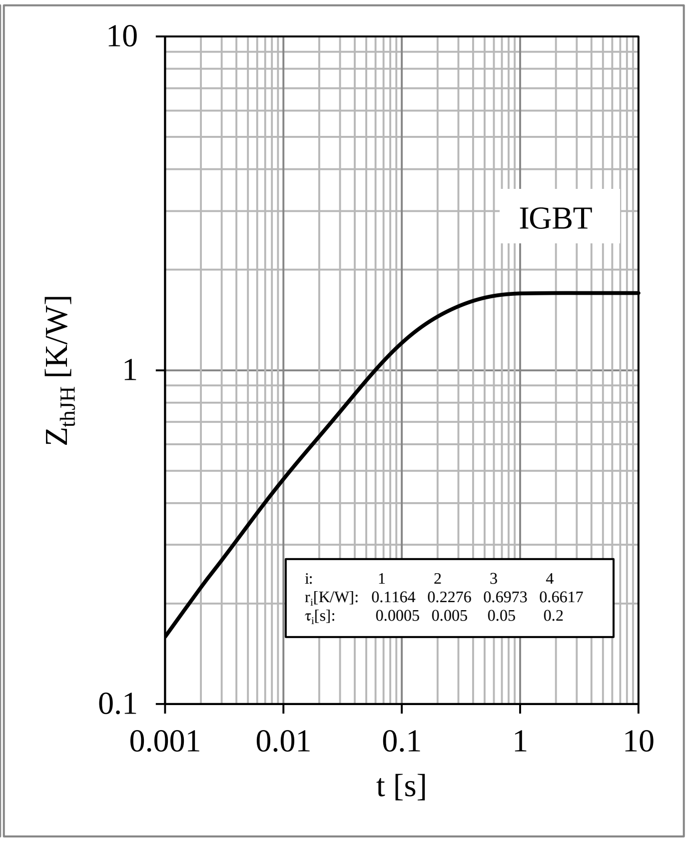


Fig 6. IGBT-inverter Transient Thermal Impedance

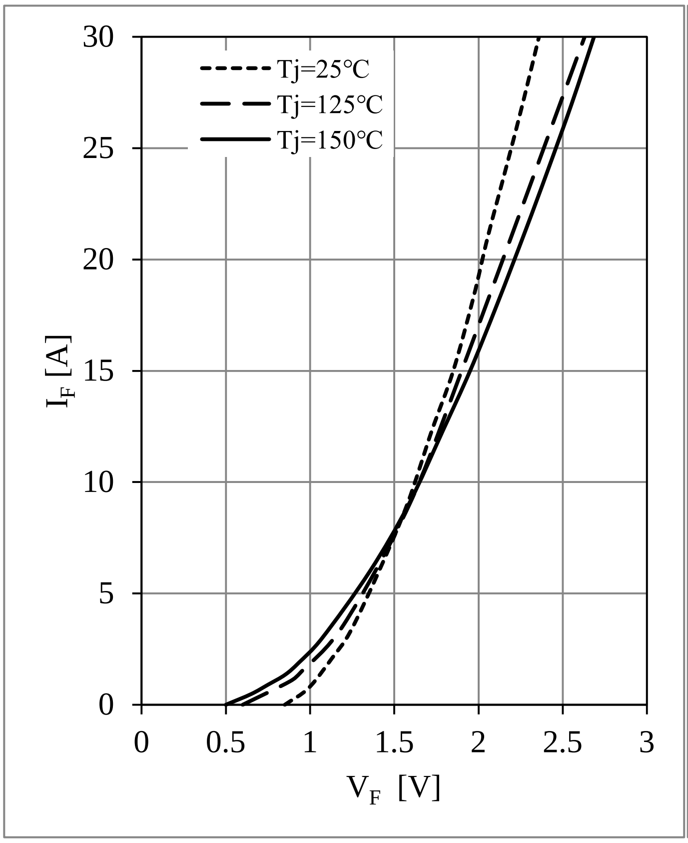


Fig 7. Diode-inverter Forward Characteristics

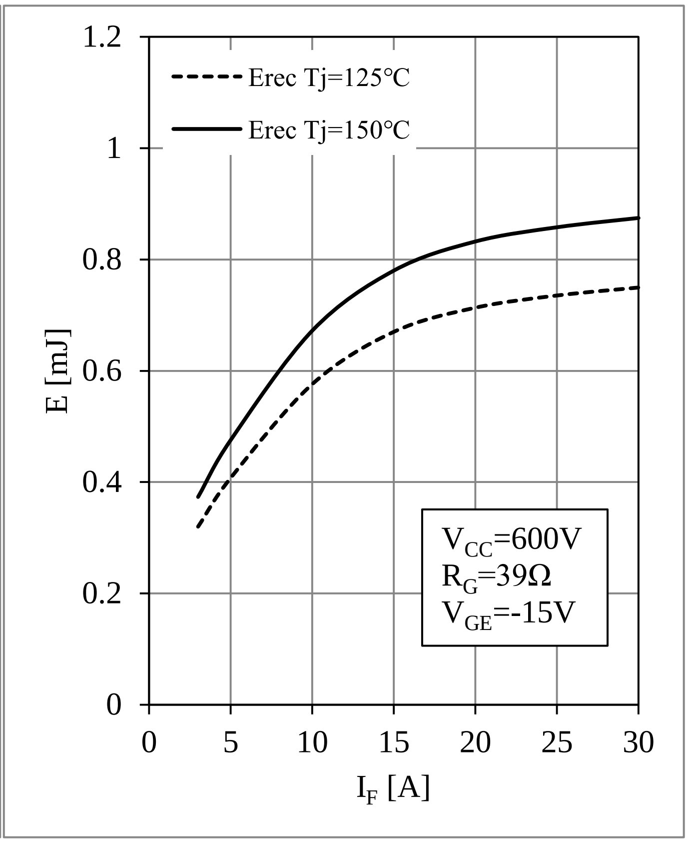


Fig 8. Diode-inverter Switching Loss vs. I_F

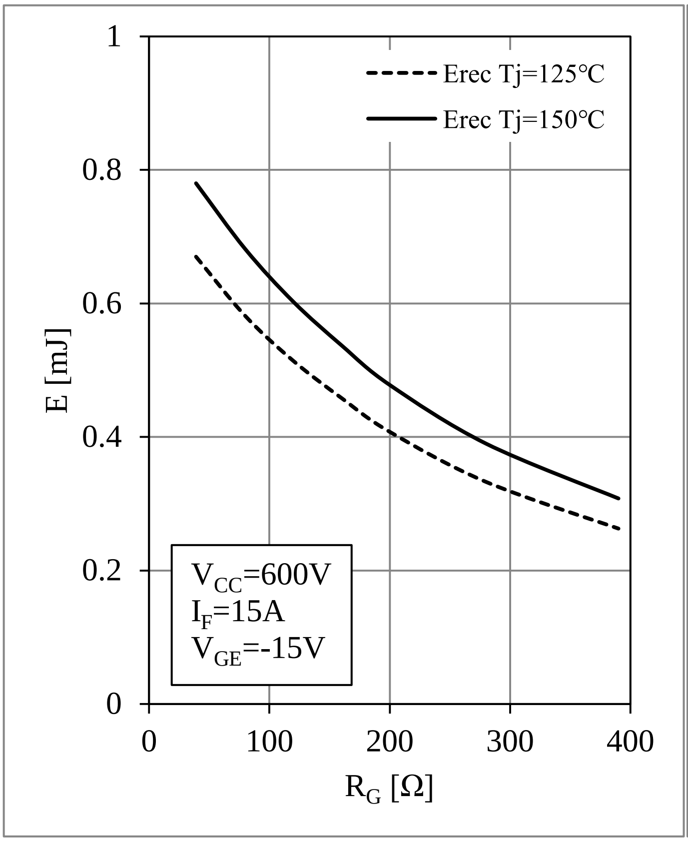


Fig 9. Diode-inverter Switching Loss vs. R_G

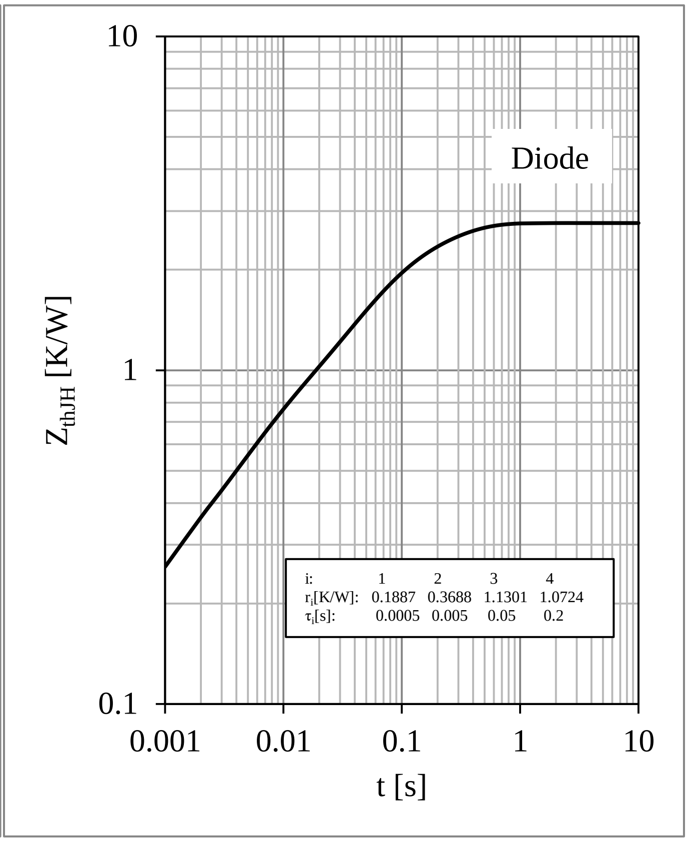


Fig 10. Diode-inverter Transient Thermal Impedance

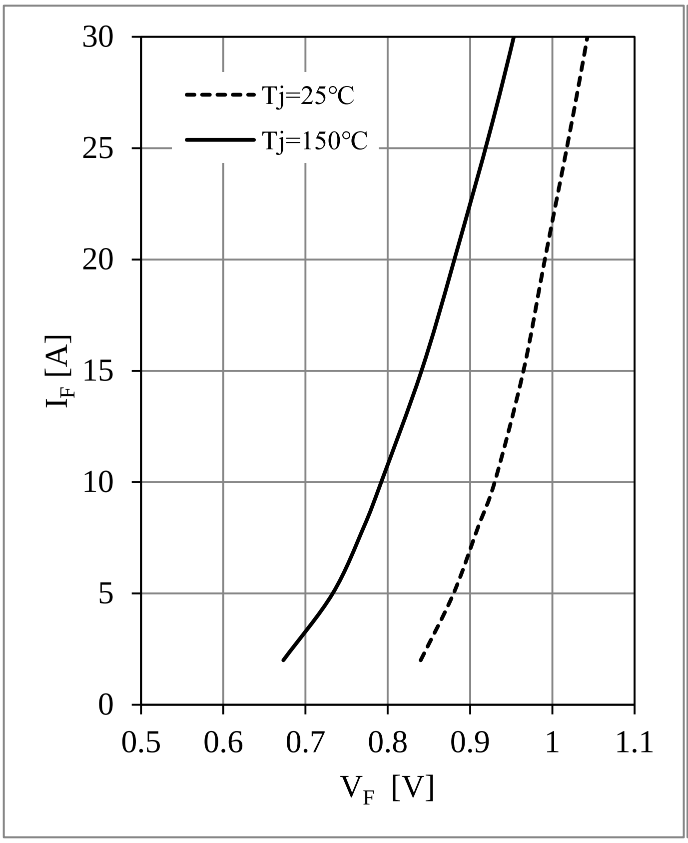


Fig 11. Diode-rectifier Forward Characteristics

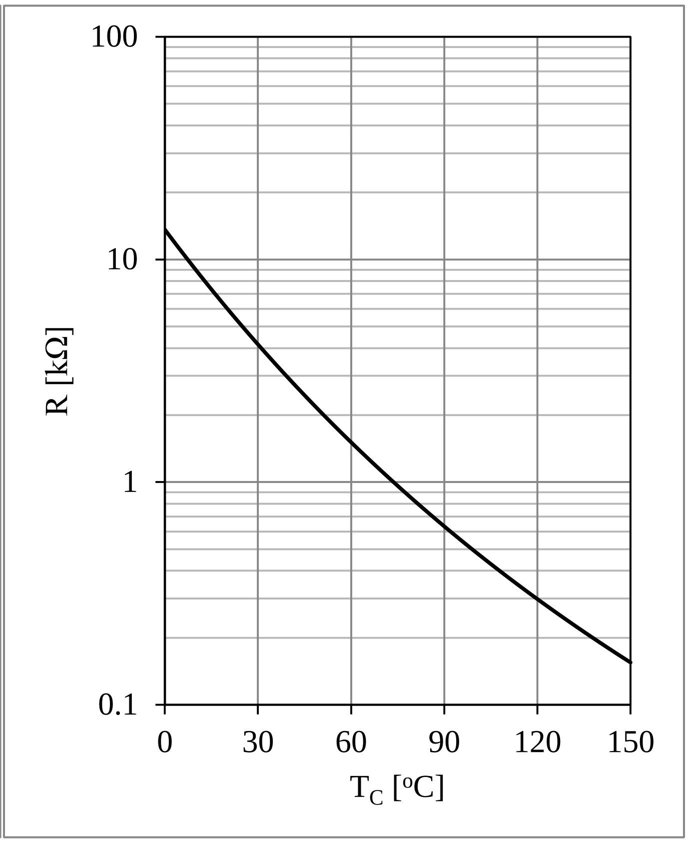
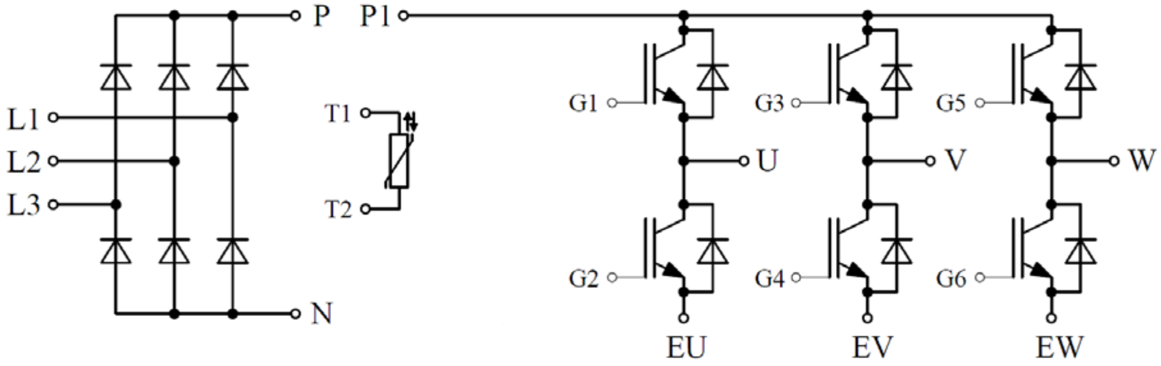


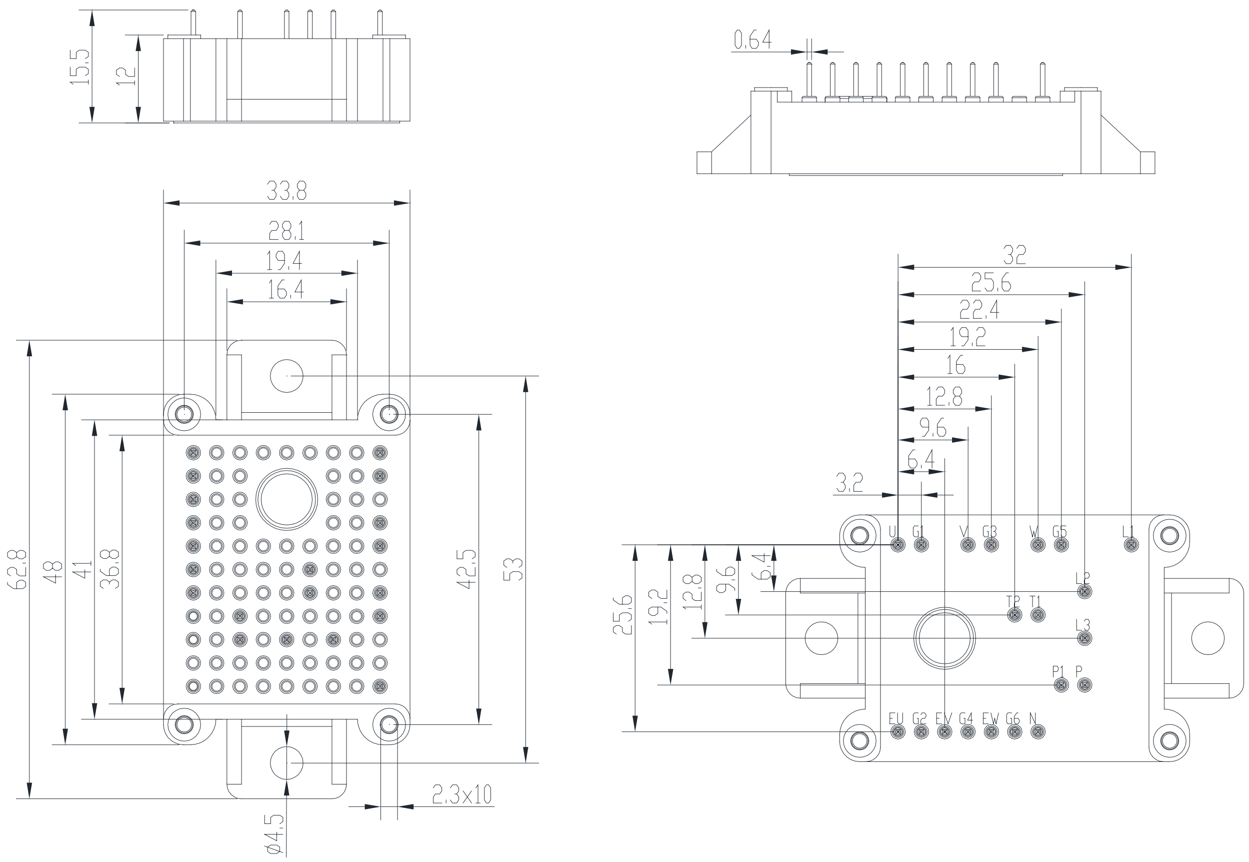
Fig 12. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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